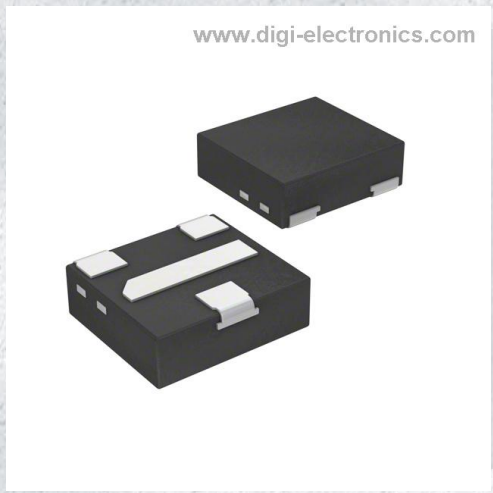
PMXB360ENEAZ Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	PMXB360ENEAZ-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	PMXB360ENEAZ
Description	MOSFET N-CH 80V 1.1A DFN1010D-3
Detailed Description	N-Channel 80 V 1.1A (Ta) 400mW (Ta), 6.25W (Tc) Surface Mount DFN1010D-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMXB360ENEAZ	Nexperia USA Inc.
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
80 V	1.1A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	450mOhm @ 1.1A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.7V @ 250µA	4.5 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	130 pF @ 40 V
FET Feature:	Power Dissipation (Max):
-	400mW (Ta), 6.25W (Tc)
Operating Temperature:	Grade:
-55°C ~ 150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Supplier Device Package:	Package / Case:
DFN1010D-3	3-XDFN Exposed Pad
Base Product Number:	
PMXB360	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

PMXB360ENEA

80 V, N-channel Trench MOSFET

5 July 2018 **Product data sheet**

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Tin-plated 100 % solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- Relay driver
- Power management in automotive and industrial applications
- LED driver
- DC-to-DC converter

4. Quick reference data

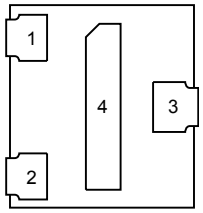
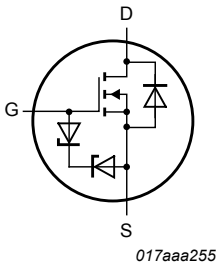
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	80	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C	[1]	-	-	1.1	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 1.1 A; T_j = 25 °C		-	345	450	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 Transparent top view **DFN1010D-3 (SOT1215)**	
2	S	source		
3	D	drain		
4	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMXB360ENEA	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215

7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB360ENEA	11 10 10

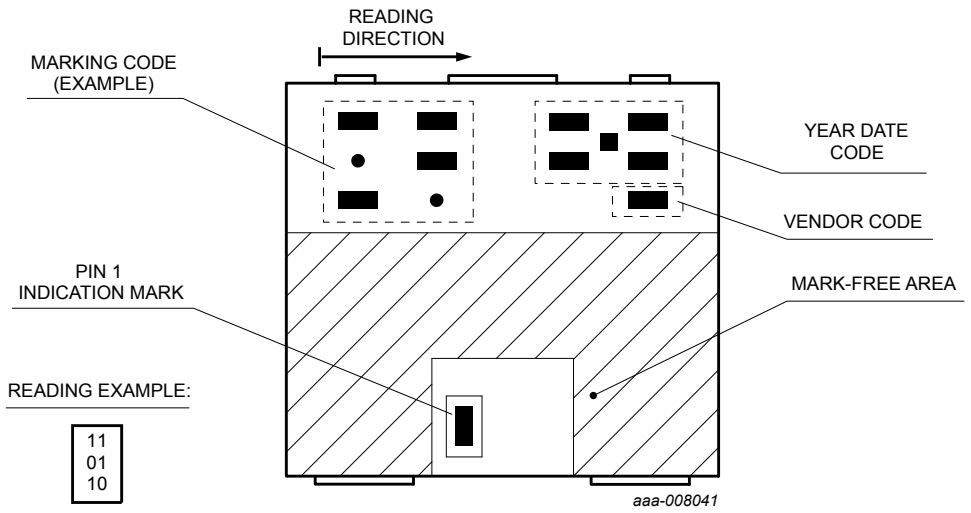


Fig. 1. DFN1010D-3 (SOT1215) binary marking code description

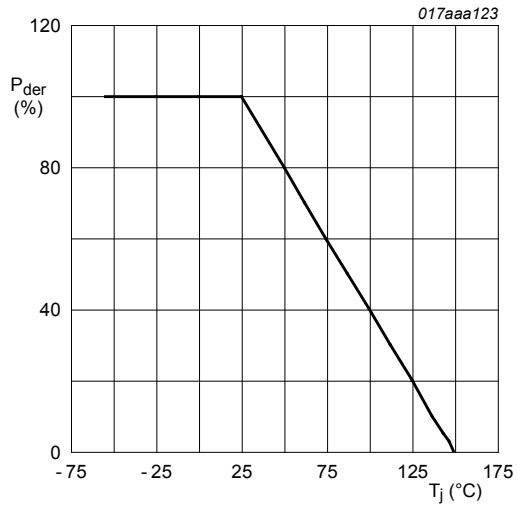
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

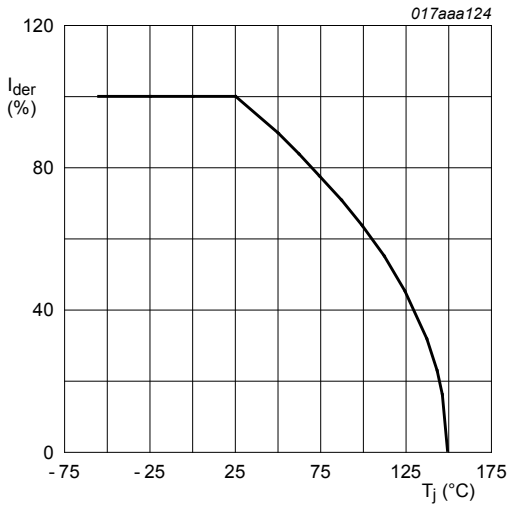
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	80	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C	[1]	-	1.1	A
		V_{GS} = 10 V; T_{amb} = 100 °C	[1]	-	0.7	A
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \leq$ 10 µs		-	4.4	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	400	mW
			[1]	-	1070	mW
		T_{sp} = 25 °C		-	6250	mW
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	0.8	A
ESD maximum rating						
V_{ESD}	electrostatic discharge voltage	HBM	[3]	-	2000	V
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.17 A; DUT in avalanche (unclamped)		-	7.1	mJ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
[3] Measured between all pins.



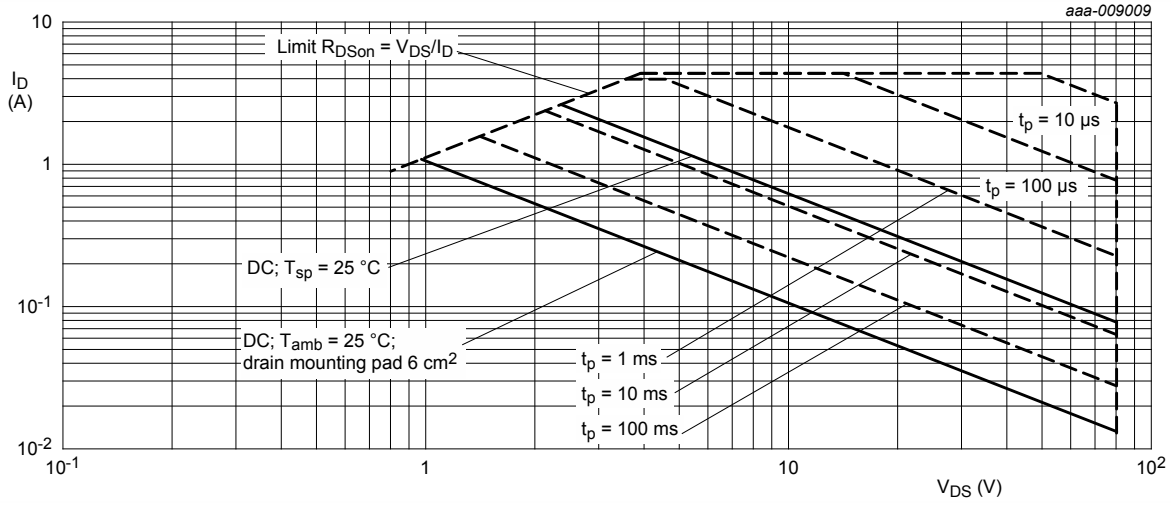
$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

Fig. 2. Normalized total power dissipation as a function of junction temperature



$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$

Fig. 3. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

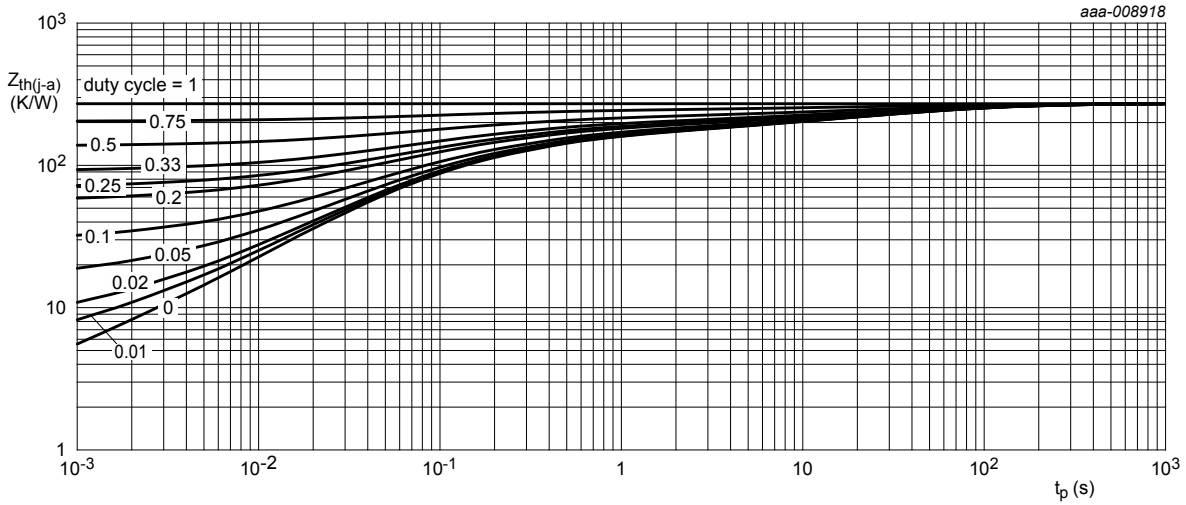
Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

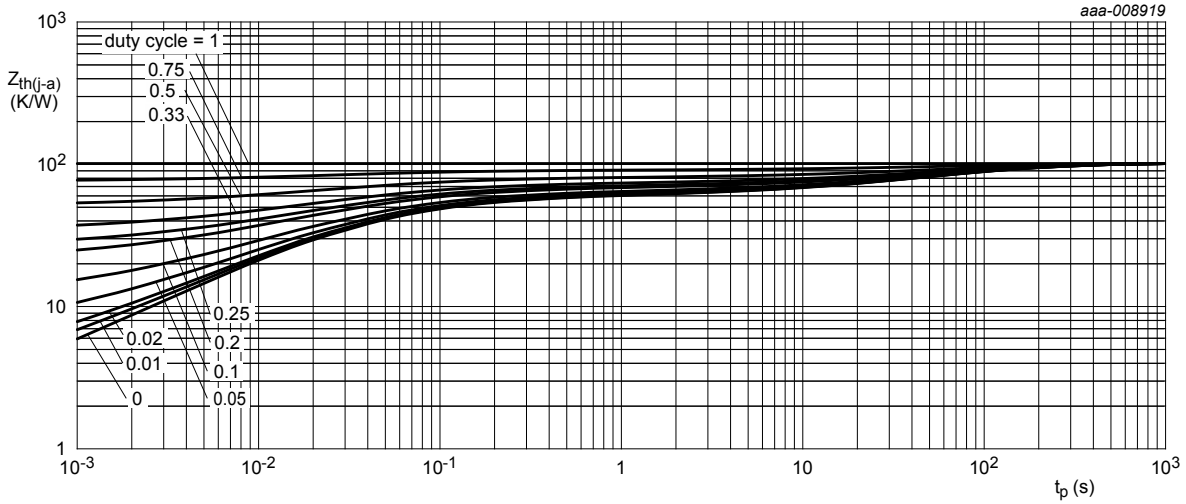
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	271	312	K/W
			[2]	-	102	117	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	15	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2.



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



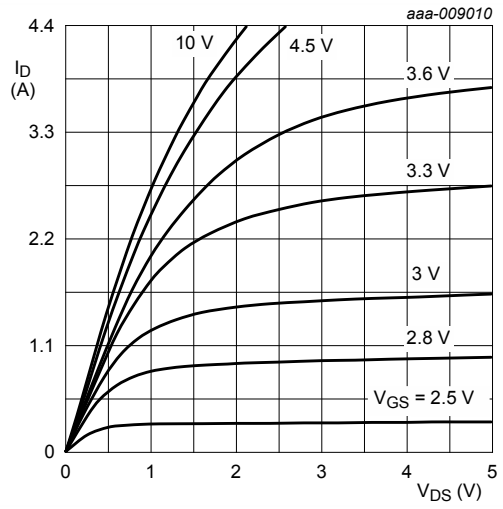
FR4 PCB, mounting pad for drain 6 cm^2

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

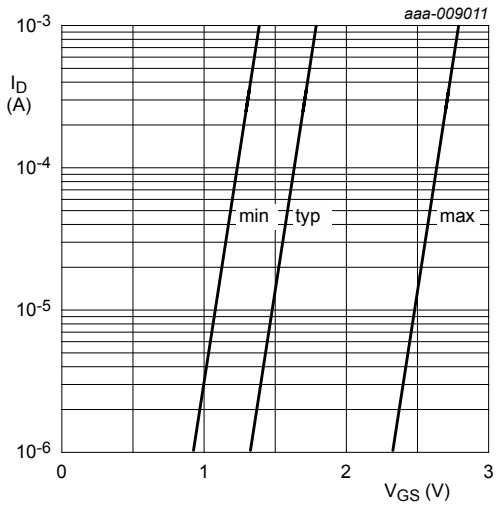
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		80	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS}=V_{GS}; T_j = 25 °C		1.3	1.7	2.7	V
I_{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	15	µA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-15	µA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C		-	-	1	µA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-1	µA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 1.1 A; T_j = 25 °C		-	345	450	mΩ
		V_{GS} = 10 V; I_D = 1.1 A; T_j = 150 °C		-	660	887	mΩ
		V_{GS} = 4.5 V; I_D = 1 A; T_j = 25 °C		-	390	540	mΩ
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 1.1 A; T_j = 25 °C		-	3.2	-	S
R_G	gate resistance	f = 1 MHz; T_j = 25 °C		-	13	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{DS} = 40 V; I_D = 1.1 A; V_{GS} = 10 V; T_j = 25 °C		-	3	4.5	nC
Q_{GS}	gate-source charge			-	0.4	-	nC
Q_{GD}	gate-drain charge			-	0.6	-	nC
C_{iss}	input capacitance	V_{DS} = 40 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	130	-	pF
C_{oss}	output capacitance			-	20	-	pF
C_{rss}	reverse transfer capacitance			-	11	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 40 V; I_D = 1.1 A; V_{GS} = 10 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C		-	2	-	ns
t_r	rise time			-	3.5	-	ns
$t_{d(off)}$	turn-off delay time			-	9	-	ns
t_f	fall time			-	3	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 0.8 A; V_{GS} = 0 V; T_j = 25 °C		-	0.8	1.2	V



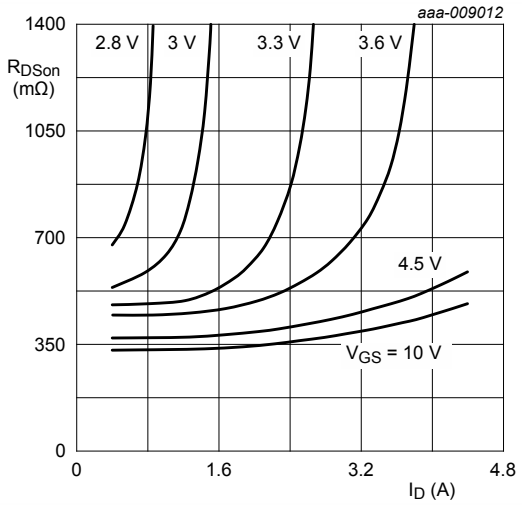
T_j = 25 °C

Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values



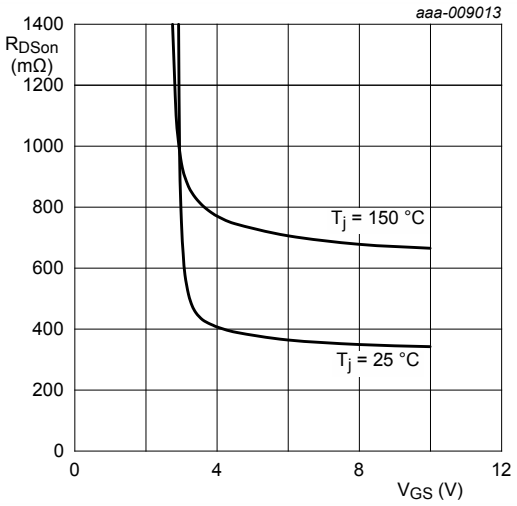
T_j = 25 °C; V_{DS} = 10 V

Fig. 8. Sub-threshold drain current as a function of gate-source voltage



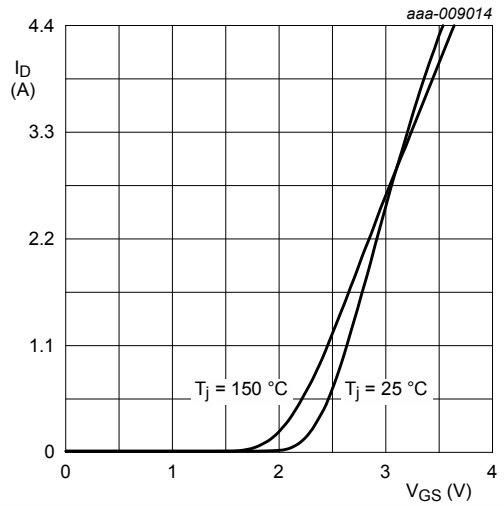
T_j = 25 °C

Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



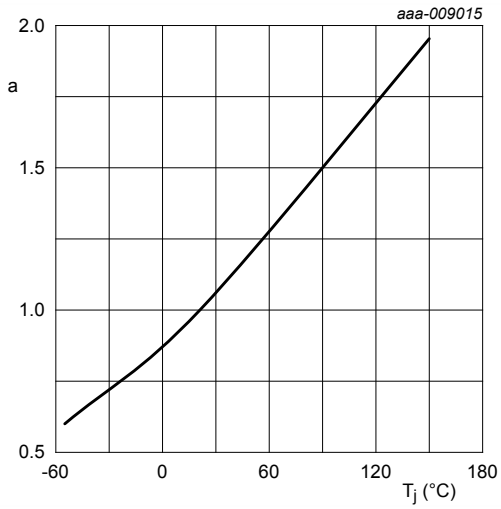
I_D = 1.1 A

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



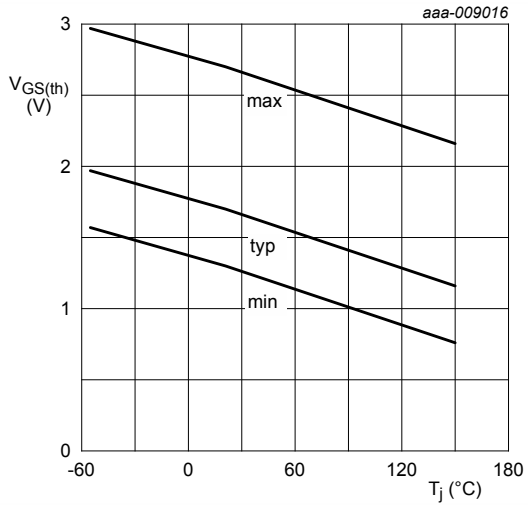
$V_{DS} > I_D \times R_{DSon}$

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values



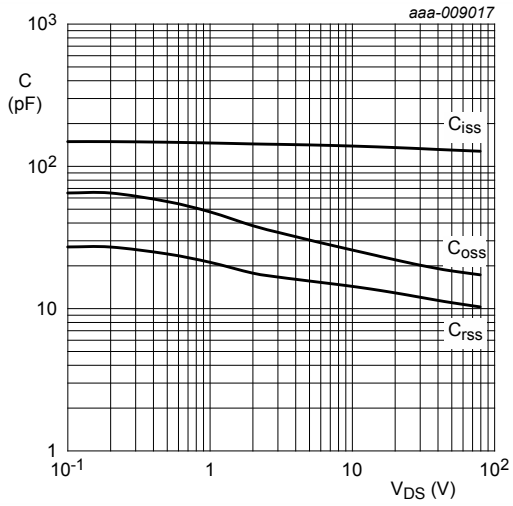
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values



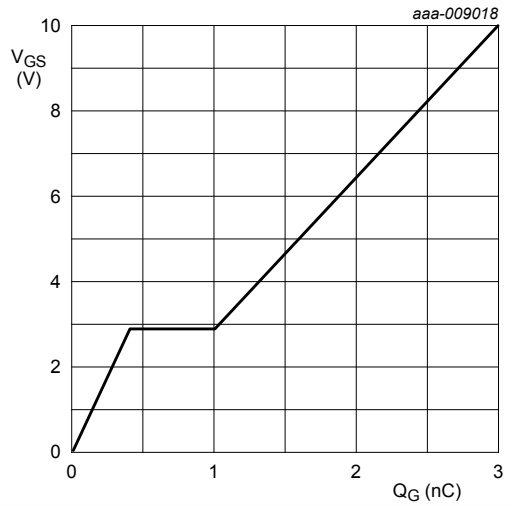
I_D = 0.25 mA; $V_{DS} = V_{GS}$

Fig. 13. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V_{GS} = 0 V

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



I_D = 1.1 A; V_{DS} = 40 V; T_{amb} = 25 °C

Fig. 15. Gate-source voltage as a function of gate charge; typical values

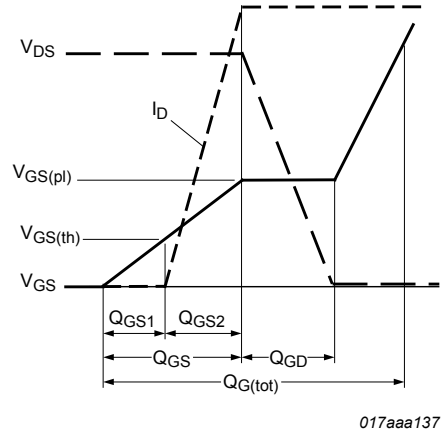
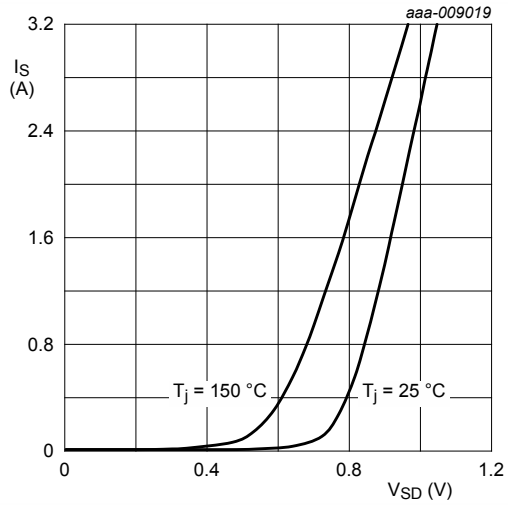


Fig. 16. MOSFET transistor: Gate charge waveform definitions



V_{GS} = 0 V

Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

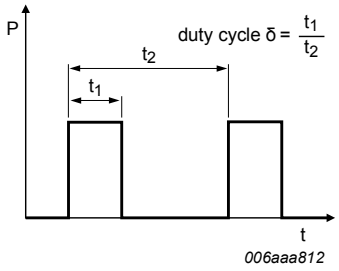


Fig. 18. Duty cycle definition

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

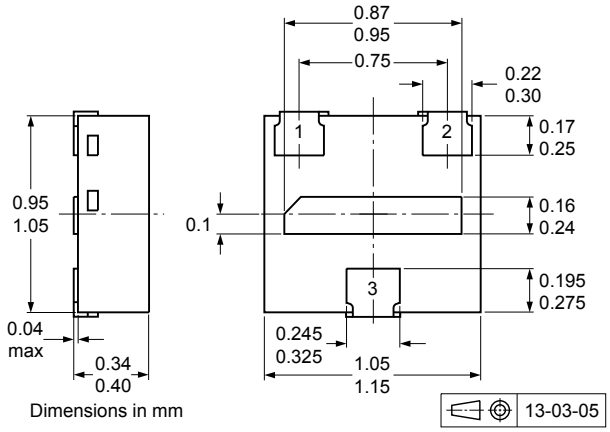


Fig. 19. Package outline DFN1010D-3 (SOT1215)

13. Soldering

Footprint information for reflow soldering of DFN1010D-3 package **SOT1215**

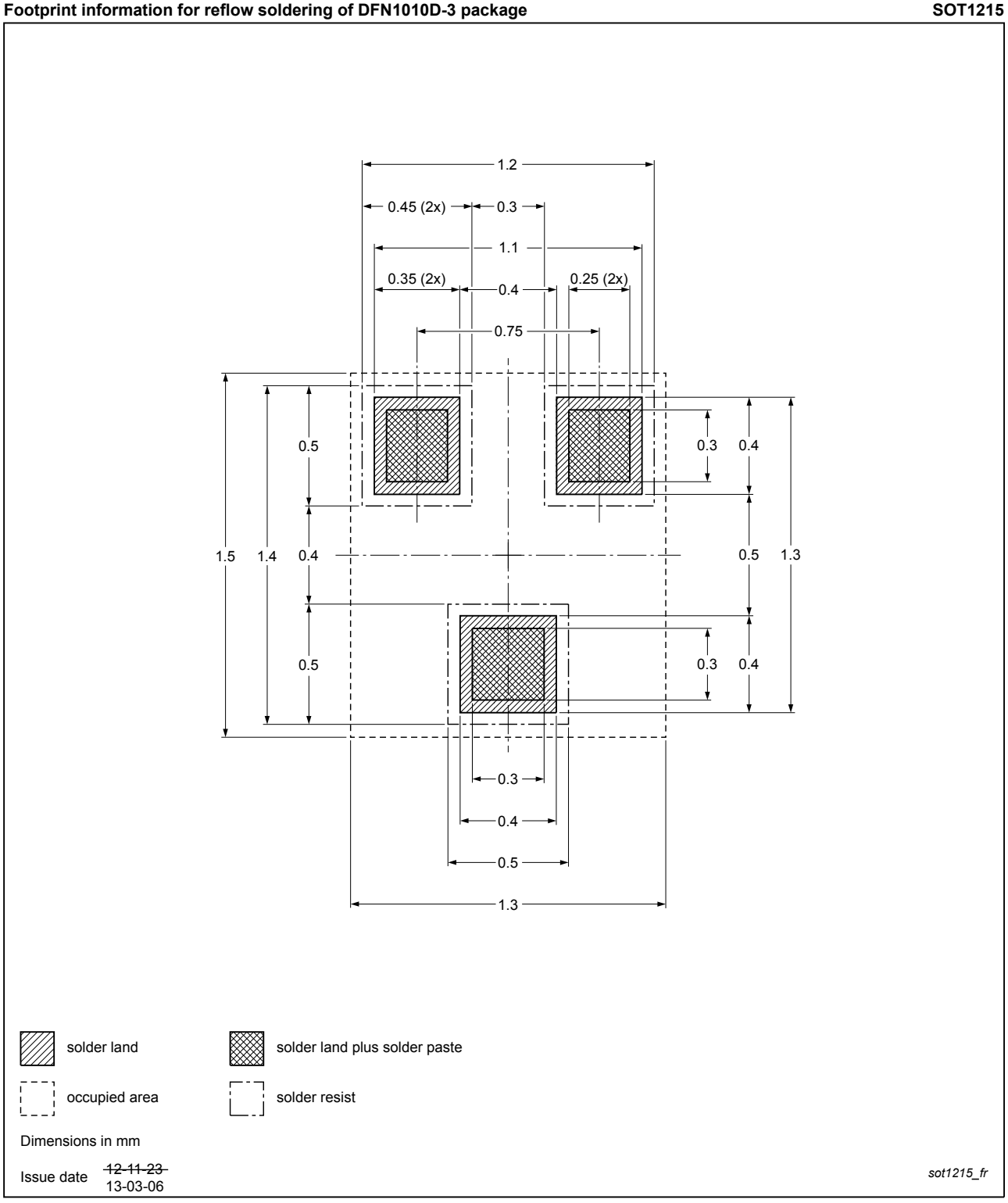


Fig. 20. Reflow soldering footprint for DFN1010D-3 (SOT1215)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMXB360ENEA v.2	20180705	Product data sheet	-	PMXB360ENEA v.1
Modification:	• Gate resistance changed to R_G 13 Ω			
PMXB360ENEA v.1	20130916	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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